~~CLAIMS~~

1. A chamber cleaning gas comprising at least one gas selected from the group consisting of $CF_3CF=CF_2$, CF_3CF-CF_2 (O) and $CF_3C(=O)CF_3$.

2. A chamber cleaning gas according to claim 1 comprising $CF_3CF=CF_2$.

3. A chamber cleaning gas according to claim 1 comprising hexafluoropropylene oxide represented by the formula CF_3CF-CF_2 (O).

4. A chamber cleaning gas according to claim 1 comprising CF_3COCF_3.

5. A chamber cleaning gas according to ~~any one of~~ claim 1 ~~claims 1-4~~ which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar, H_2, N_2 and O_2.

6. A chamber cleaning method comprising the step of treating a plasma CVD chamber of a semiconductor integrated circuit production device with at least one chamber cleaning gas selected from the group consisting of $CF_3CF=CF_2$, CF_3CF-CF_2 (O) and $CF_3C(=O)CF_3$.

7. A chamber cleaning method according to claim 6 wherein the chamber cleaning gas is $CF_3CF=CF_2$.

8. A chamber cleaning method according to claim 6 wherein the chamber cleaning gas is hexafluoropropylene oxide represented by the formula $CF_3CF\text{-}CF_2$ (with O).

9. A chamber cleaning method according to claim 6 wherein the chamber cleaning gas is CF_3COCF_3.

10. A chamber cleaning gas according to ~~any one of claims 6-9~~ claim 6 which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar, H_2, N_2 and O_2.